



HMPSA42

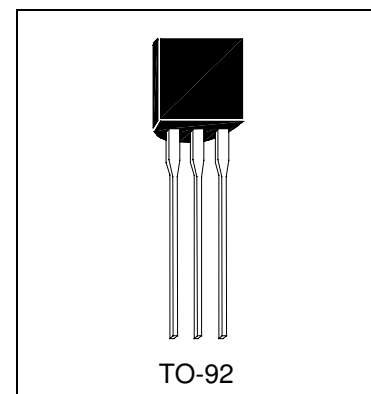
NPN EPITACIAL PLANAR TRANSISTOR

Description

The HMPSA42 is high voltage transistor.

Features

- High Collector-Emitter Breakdown Voltage
- Low Collector-Emitter Saturation Voltage
- For Complementary Use with PNP Type HMPSA92



TO-92

Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature -55 ~ +150 °C
Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation ($T_A=25^{\circ}\text{C}$) 625 mW
- Maximum Voltages and Currents ($T_A=25^{\circ}\text{C}$)
 V_{CBO} Collector to Base Voltage 300 V
 V_{CEO} Collector to Emitter Voltage 300 V
 V_{EBO} Emitter to Base Voltage 6 V
 I_C Collector Current 500 mA

Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	300	-	-	V	$I_C=100\mu\text{A}$, $I_E=0$
BV_{CEO}	300	-	-	V	$I_C=1\text{mA}$, $I_B=0$
BV_{EBO}	6	-	-	V	$I_E=10\mu\text{A}$, $I_C=0$
I_{CBO}	-	-	100	nA	$V_{CB}=260\text{V}$, $I_E=0$
I_{EBO}	-	-	100	nA	$V_{EB}=6\text{V}$, $I_C=0$
$^*V_{CE(sat)}$	-	-	350	mV	$I_C=20\text{mA}$, $I_B=2\text{mA}$
$^*V_{BE(sat)}$	-	-	900	mV	$I_C=20\text{mA}$, $I_B=2\text{mA}$
$^*h_{FE1}$	25	-	-		$I_C=1\text{mA}$, $V_{CE}=10\text{V}$
$^*h_{FE2}$	40	-	-		$I_C=10\text{mA}$, $V_{CE}=10\text{V}$
$^*h_{FE3}$	40	-	-		$I_C=30\text{mA}$, $V_{CE}=10\text{V}$
f_T	50	-	-	MHz	$I_C=10\text{mA}$, $V_{CE}=20\text{V}$, $f=100\text{MHz}$
Cob	-	-	3	pF	$V_{CB}=20\text{V}$, $f=1\text{MHz}$, $I_E=0$

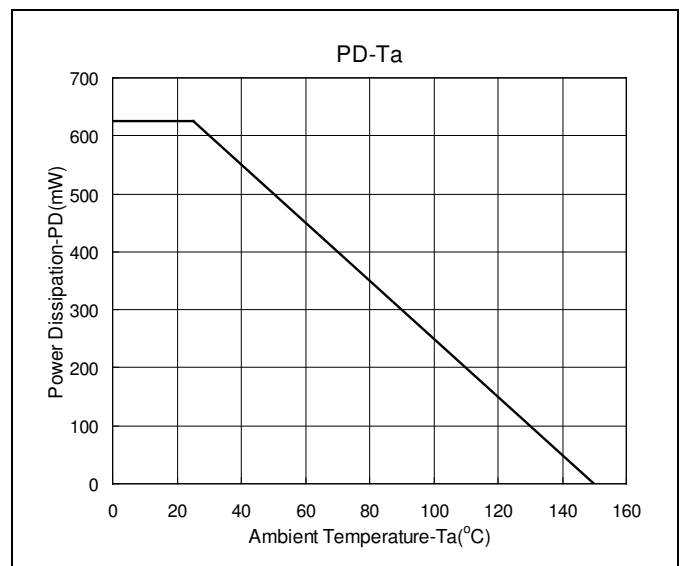
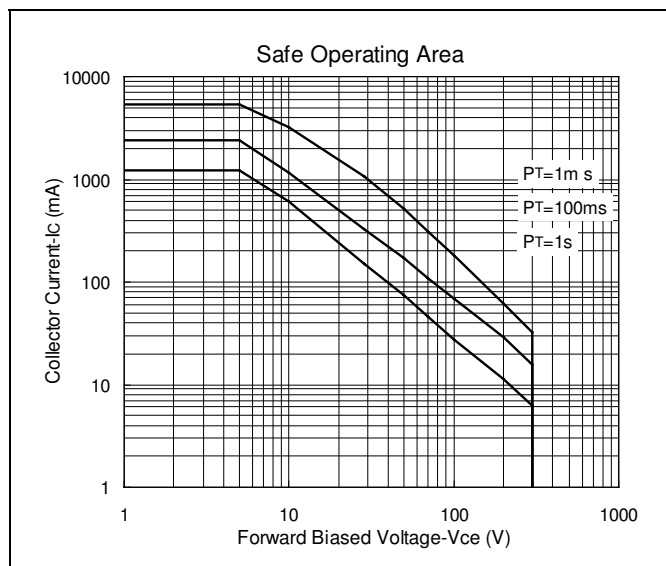
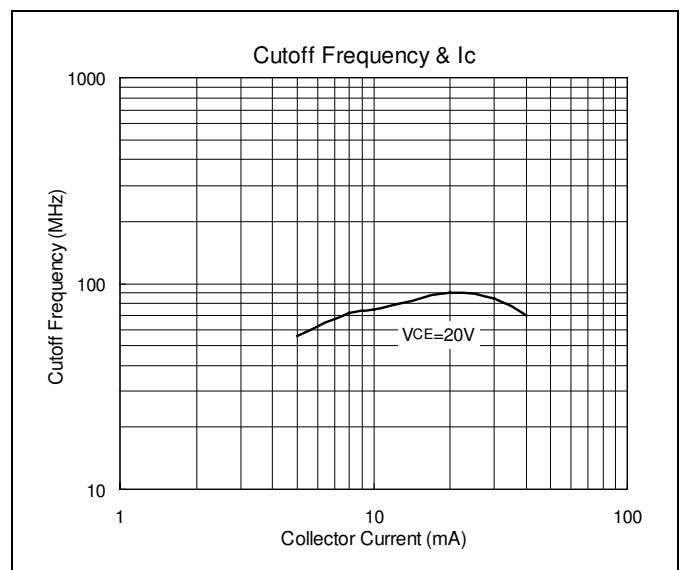
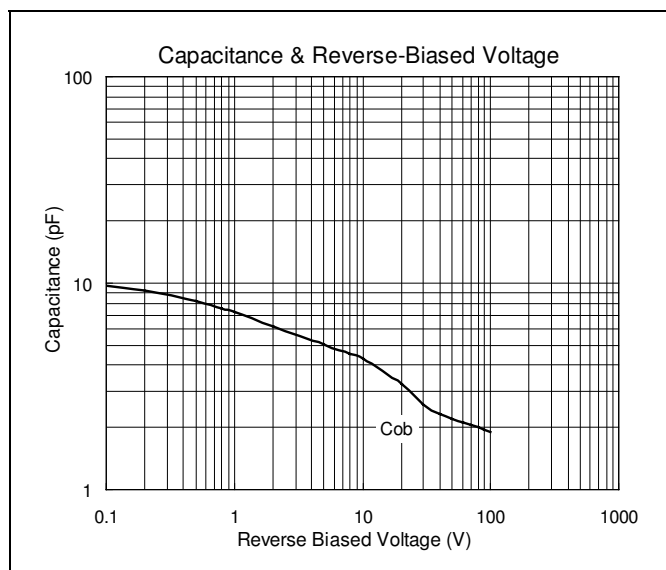
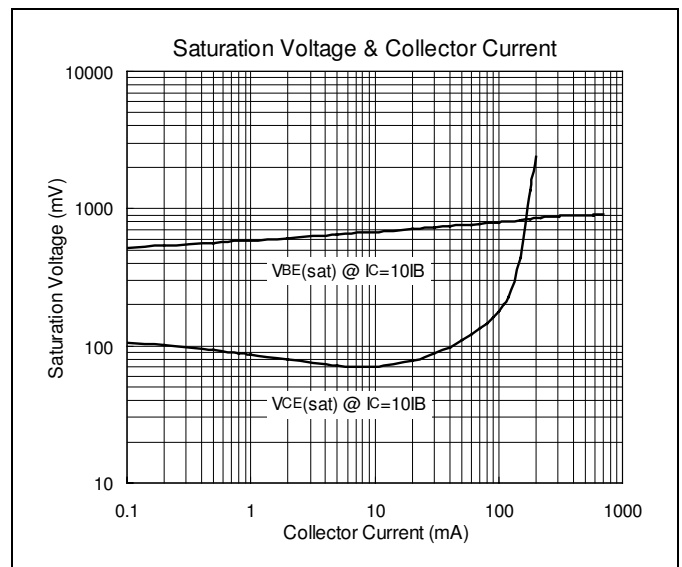
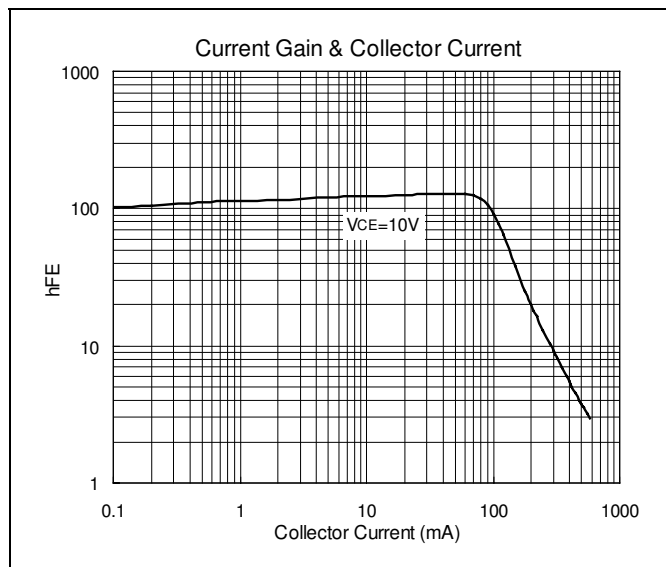
*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

Classification Of Rank

Rank	h_{FE1}	h_{FE2}	h_{FE3}	$V_{CE(sat)}$
NS	>80	>120	>120	<200mV
N	>25	>40	>40	<350mV

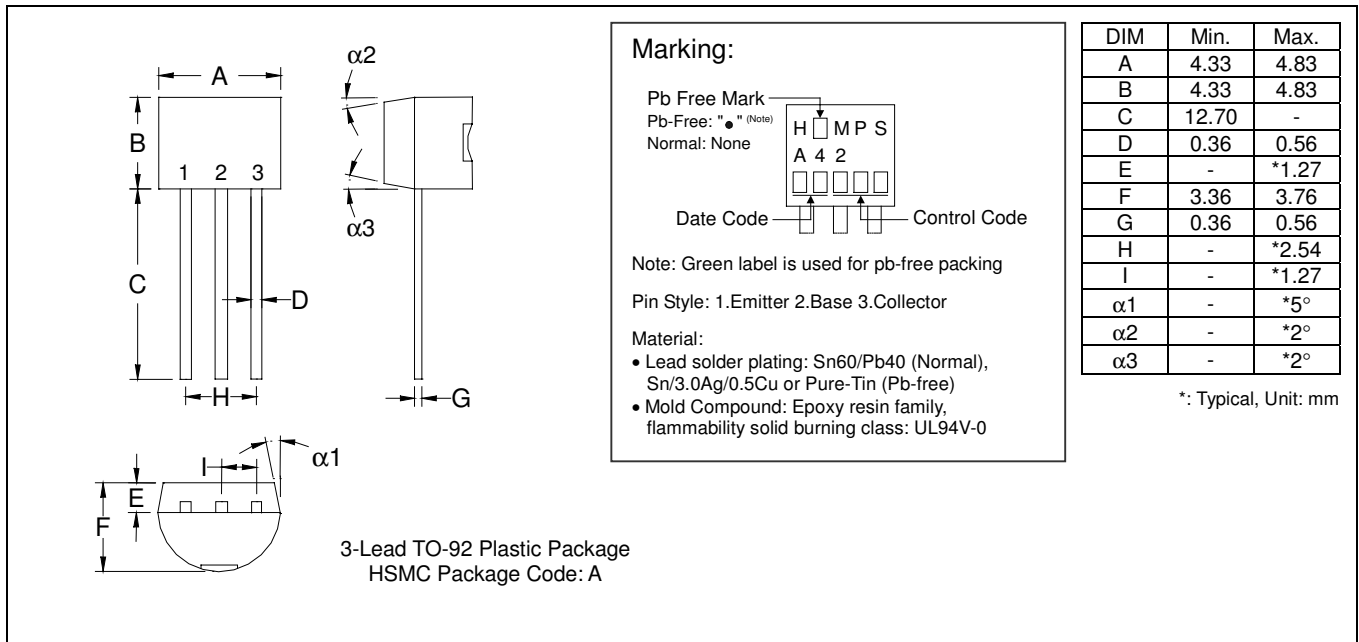


Characteristics Curve

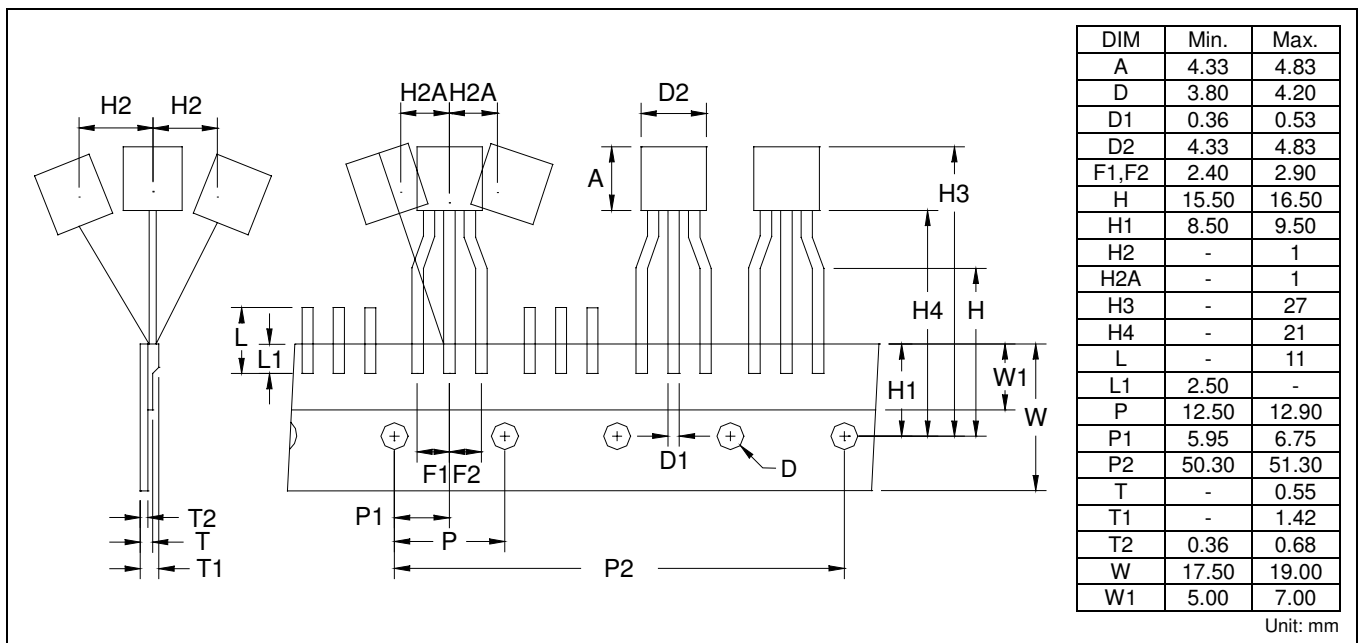




TO-92 Dimension



TO-92 Taping Dimension



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Head Office And Factory:

- Head Office** (Hi-Sincerity Microelectronics Corp.): 10F., No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
Tel: 886-3-5983621~5 Fax: 886-3-5982931

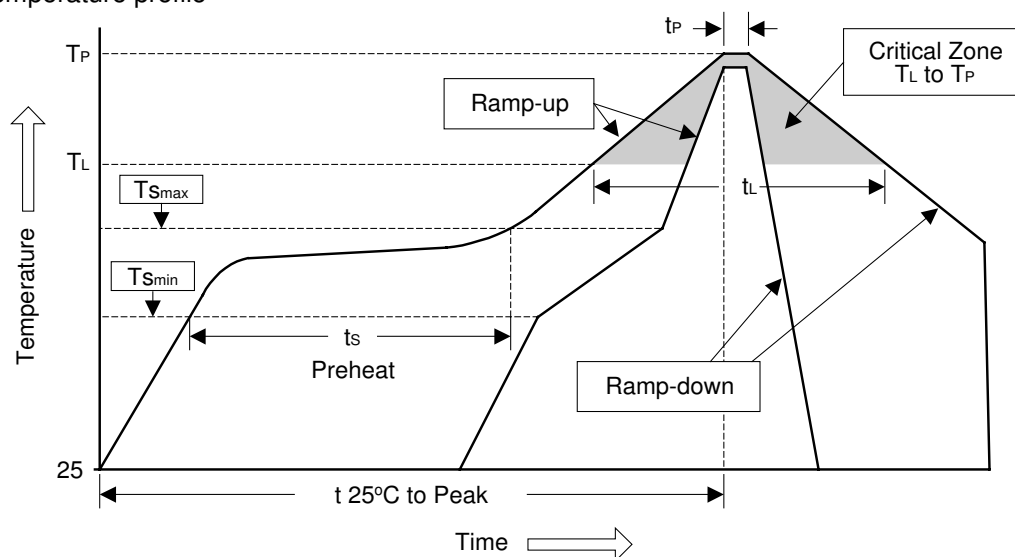


Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%

2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec